Correction to: Impact Ionization Induced by Terahertz Radiation in HgTe QuantumWells of Critical Thickness

S. Hubmann¹ · G. V. Budkin² · M. Urban¹ · V. V. Bel'kov² · A. P. Dmitriev² · J. Ziegler¹ · D. A. Kozlov³ · N. N. Mikhailov³ · S. A. Dvoretzky³ · Z. D. Kvon³ · D. Weiss¹ · S. D. Ganichev¹

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The original article has been corrected.

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✉ S. D. Ganichev
sergey.ganichev@ur.de

¹ Terahertz Center, University of Regensburg, 93040 Regensburg, Germany

² Ioffe Institute, 194021 St. Petersburg, Russia

³ Rzhanov Institute of Semiconductor Physics, 630090 Novosibirsk, Russia

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